ABSTRACT OF THE DISCLOSURE

A semiconductor device and a method for making the same that provide highly reliable and high density arrangement of a connecting region for an external connecting terminal, such as a bonding pad. Electrode layers are connected to each other through embedded conductive layers forming highly-superposed multi-layered structures without bumps. Openings are provided in a second electrode layer, a first insulating interlayer and a second insulating interlayer. The above layers are connected to each other through openings. A prop of the insulating interlayer film is formed between the third electrode layer and the first electrode layer. The props prevent cracks from forming in the insulating interlayers when a load is applied during wire-bonding.